

## FDD6644/FDU6644

### 30V N-Channel PowerTrench® MOSFET

#### General Description

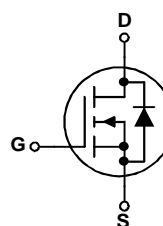
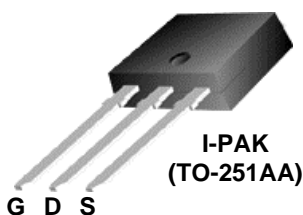
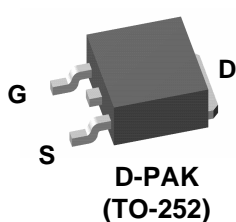
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

#### Applications

- DC/DC converter

#### Features

- 67 A, 30 V.  $R_{DS(ON)} = 8.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 10.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- High performance trench technology for extremely low  $R_{DS(ON)}$
- Low gate charge (25 nC typical)
- High power and current handling capability



#### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 16$	V
$I_D$	Drain Current – Continuous (Note 1a)	67	A
	– Pulsed	100	
$P_D$	Maximum Power Dissipation (Note 1)	68	W
		3.8	
		1.6 (Note 1b)	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$

#### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	2.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	$^\circ\text{C/W}$

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape width	Quantity
FDD6644	FDD6644	D-PAK (TO-252)	13"	12mm	2500 units
FDU6644	FDU6644	I-PAK (TO-251)	Tube	N/A	75

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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#### Drain-Source Avalanche Ratings (Note 2)

$W_{DSS}$	Drain-Source Avalanche Energy	Single Pulse, $V_{DD} = 15\text{ V}$ , $I_D = 17\text{ A}$			240	mJ
$I_{AR}$	Drain-Source Avalanche Current				17	A

#### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		27		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 16\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -16\text{ V}$ , $V_{DS} = 0\text{ V}$			-100	nA

#### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1	1.5	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$ $V_{GS} = 4.5\text{ V}$ , $I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 16.5\text{ A}$ , $T_J = 125^\circ\text{C}$		6.5 7.5 10	8.5 10.5 13	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 5\text{ V}$	50			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 16\text{ A}$		74		S

#### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		3087		pF
$C_{oss}$	Output Capacitance			489		pF
$C_{riss}$	Reverse Transfer Capacitance			185		pF

#### Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$ , $I_D = 1\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\ \Omega$		10	20	ns
$t_r$	Turn-On Rise Time			12	22	ns
$t_{d(off)}$	Turn-Off Delay Time			48	77	ns
$t_f$	Turn-Off Fall Time			10	20	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}$ , $I_D = 16\text{ A}$ , $V_{GS} = 5\text{ V}$		25	35	nC
$Q_{gs}$	Gate-Source Charge			7.5		
$Q_{gd}$	Gate-Drain Charge			6.5		

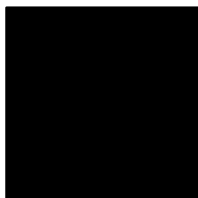
**Electrical Characteristics** (continued)  $T_A = 25^\circ\text{C}$  unless otherwise noted

**Drain–Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain–Source Diode Forward Current			3.2	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.7\text{ A}$ (Note 2)		0.7	1.2
					V

**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $R_{\theta JA} = 40^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $R_{\theta JA} = 96^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty Cycle  $< 2.0\%$

- Maximum current is calculated as: 
$$\sqrt{\frac{P_D}{R_{DS(ON)}}}$$

where  $P_D$  is maximum power dissipation at  $T_C = 25^\circ\text{C}$  and  $R_{DS(on)}$  is at  $T_{J(max)}$  and  $V_{GS} = 10\text{V}$ . Package current limitation is 21A

### Typical Characteristics

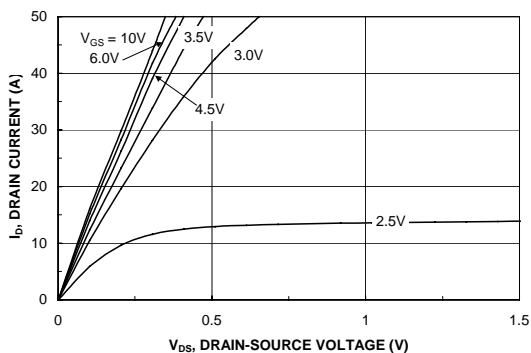


Figure 1. On-Region Characteristics.

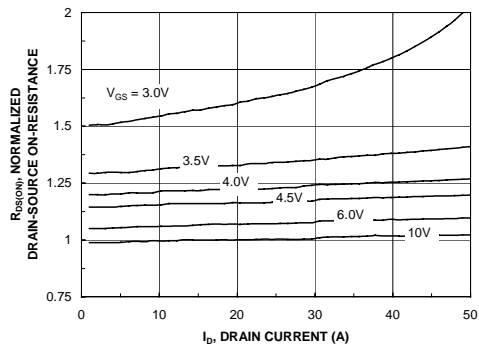


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

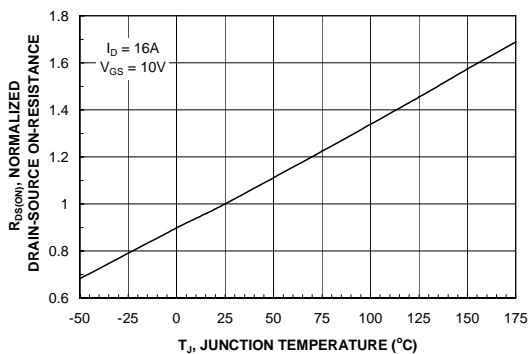


Figure 3. On-Resistance Variation with Temperature.

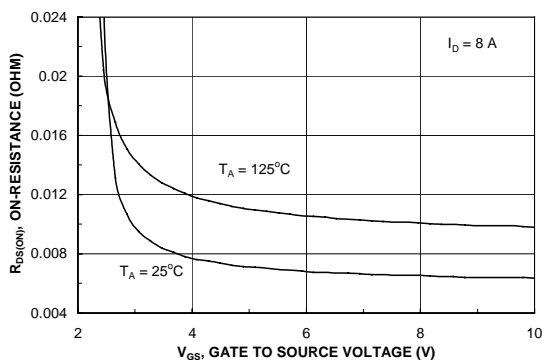


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

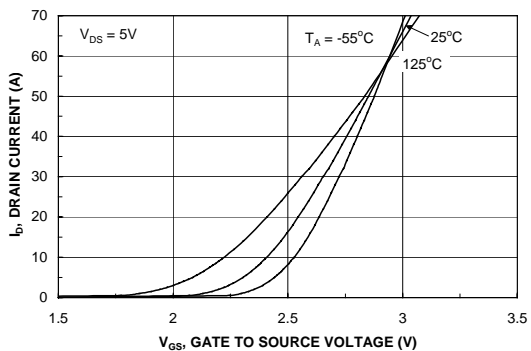


Figure 5. Transfer Characteristics.

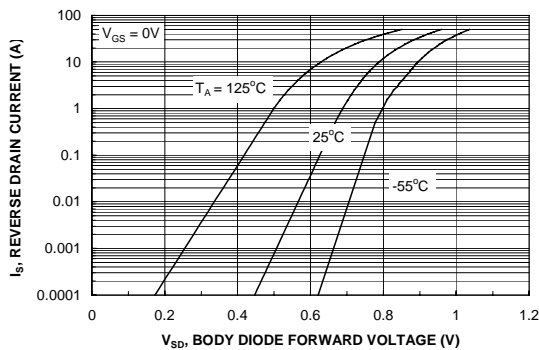


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics

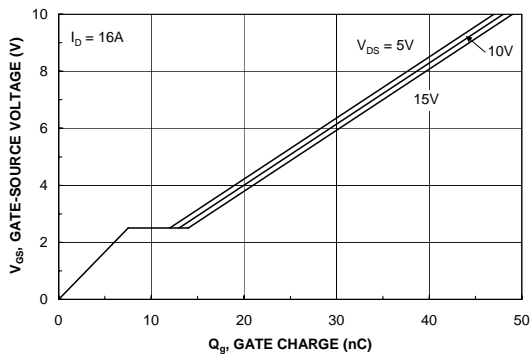


Figure 7. Gate Charge Characteristics.

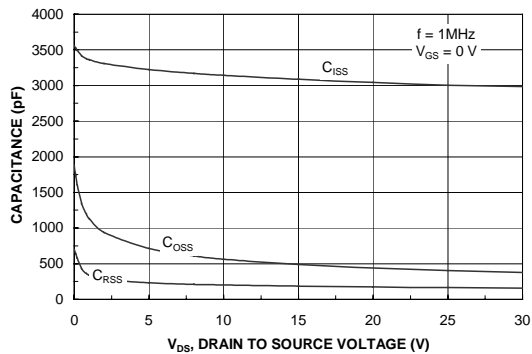


Figure 8. Capacitance Characteristics.

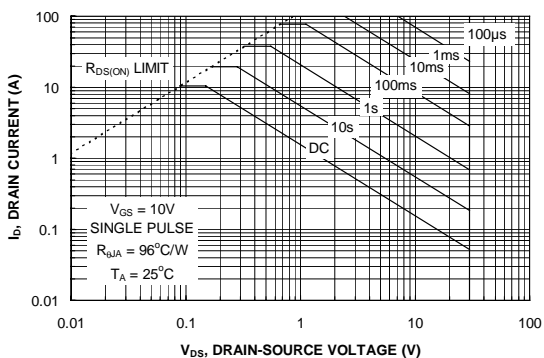


Figure 9. Maximum Safe Operating Area.

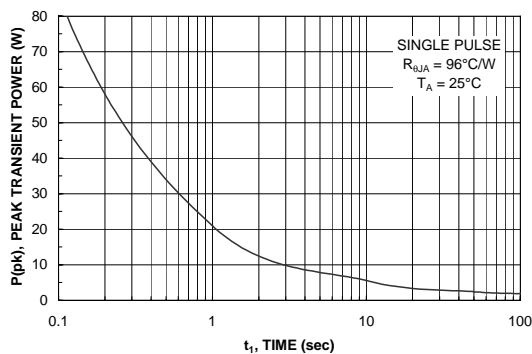


Figure 10. Single Pulse Maximum Power Dissipation.

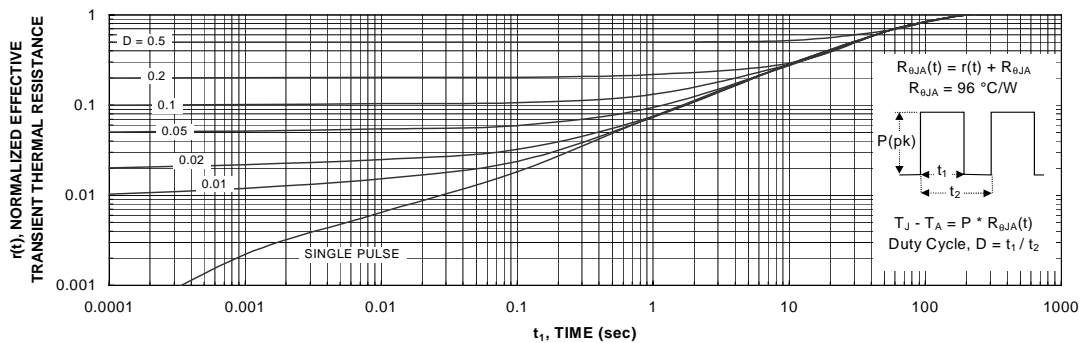


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b  
 Transient thermal response will change depending on the circuit board design.

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